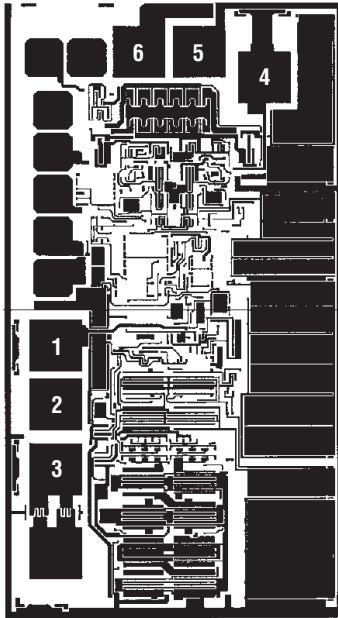


RH6200M
 Low Noise, High Speed
 Rail-to-Rail Op Amp

PAD FUNCTION

1. $\overline{\text{SHDN}}$
2. $-IN$
3. $+IN$
4. OUT
5. V^-
6. V^+

DIE CROSS REFERENCE

LTC Finished Part Number	Order DICE Part Number
RH6200MW	RH6200M DICE

LT, LT, LTC, LTM, Linear Technology and the Linear logo are registered trademarks of Linear Technology Corporation. All other trademarks are the property of their respective owners.

57mils × 33mils,
 12mils thick.
 Backside metal: Gold
 Backside potential: V^-

DICE/DWF ELECTRICAL TEST LIMITS $T_A = 25^\circ\text{C}$

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNITS
V_{OS}	Input Offset Voltage	$V_S = 5V, 0V; V_{CM} = V^- \text{ to } V^+$		2	mV
		$V_S = \pm 5V; V_{CM} = V^- \text{ to } V^+$		6	mV
I_B	Input Bias Current	$V_S = 5V, 0V; V_{CM} = V^+$		18	μA
		$V_S = 5V, 0V; V_{CM} = V^-$	-50		μA
		$V_S = \pm 5V; V_{CM} = V^+$		18	μA
		$V_S = \pm 5V; V_{CM} = V^-$	-50		μA
I_{OS}	Input Offset Current	$V_S = 5V, 0V; V_{CM} = V^+$		4	μA
		$V_S = 5V, 0V; V_{CM} = V^-$		5	μA
		$V_S = \pm 5V; V_{CM} = V^+$		7	μA
		$V_S = \pm 5V; V_{CM} = V^-$		12	μA
A_{VOL}	Large Signal Open-Loop Voltage Gain	$V_S = 5V, 0V; R_L = 1k; V_{OUT} = 0.5V \text{ to } 4.5V$	70		V/mV
		$V_S = 5V, 0V; R_L = 100\Omega; V_{OUT} = 1V \text{ to } 4V$	11		V/mV
		$V_S = \pm 5V; R_L = 1k; V_{OUT} = \pm 4.5V$	115		V/mV
		$V_S = \pm 5V; R_L = 100\Omega; V_{OUT} = \pm 2V$	15		V/mV
CMRR	Common Mode Rejection Ratio	$V_S = 5V, 0V; V_{CM} = 0V \text{ to } 5V$	65		dB
		$V_S = 5V, 0V; V_{CM} = 1.5V \text{ to } 3.5V$	85		dB
		$V_S = \pm 5V; V_{CM} = \pm 5V$	68		dB
		$V_S = \pm 5V; V_{CM} = \pm 2V$	75		dB

DICE SPECIFICATION

RH6200M

DICE/DWF ELECTRICAL TEST LIMITS $T_A = 25^\circ\text{C}$

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNITS
PSRR	Power Supply Rejection Ratio	$V_S = \pm 2.25\text{V to } \pm 5\text{V}$	60		dB
V_{OL}	Output Voltage Swing Low	$V_S = 5\text{V}, 0\text{V}; I_L = 0$		50	mV
		$V_S = 5\text{V}, 0\text{V}; I_L = 5\text{mA}$		100	mV
		$V_S = 5\text{V}, 0\text{V}; I_L = 20\text{mA}$		290	mV
		$V_S = \pm 5\text{V}; I_L = 0$		50	mV
		$V_S = \pm 5\text{V}; I_L = 5\text{mA}$		110	mV
		$V_S = \pm 5\text{V}; I_L = 20\text{mA}$		290	mV
V_{OH}	Output Voltage Swing High	$V_S = 5\text{V}, 0\text{V}; I_L = 0$		110	mV
		$V_S = 5\text{V}, 0\text{V}; I_L = 5\text{mA}$		190	mV
		$V_S = 5\text{V}, 0\text{V}; I_L = 20\text{mA}$		400	mV
		$V_S = \pm 5\text{V}; I_L = 0$		130	mV
		$V_S = \pm 5\text{V}; I_L = 5\text{mA}$		210	mV
		$V_S = \pm 5\text{V}; I_L = 20\text{mA}$		420	mV
I_{SC}	Short-Circuit Current	$V_S = 5\text{V}, 0\text{V}$ or $V_S = \pm 5\text{V}$	± 60		mA
I_S	Supply Current	$V_S = 5\text{V}, 0\text{V}$		20	mA
		$V_S = \pm 5\text{V}$		23	mA
$I_{S(SHDN)}$	Shutdown Supply Current	$V_S = 5\text{V}, 0\text{V}$		1.8	mA
		$V_S = \pm 5\text{V}$		2.1	mA
I_{SHDN}	Shutdown Pin Current	$V_S = 5\text{V}, 0\text{V}$ or $V_S = \pm 5\text{V}; V_{SHDN} = 0.3\text{V}$	-280		μA
GBW	Gain Bandwidth Product	$V_S = \pm 5\text{V};$ at $f = 1\text{MHz}$	110		MHz

Rad Hard die require special handling as compared to standard IC chips.

Rad Hard die are susceptible to surface damage because there is no silicon nitride passivation as on standard die. Silicon nitride protects the die surface from scratches by its hard and dense properties. The passivation on Rad Hard die is silicon dioxide that is much "softer" than silicon nitride.

LTC recommends that die handling be performed with extreme care so as to protect the die surface from scratches. If the need arises to move

the die around from the chip tray, use a Teflon-tipped vacuum wand. This wand can be made by pushing a small diameter Teflon tubing onto the tip of a steel-tipped wand. The inside diameter of the Teflon tip should match the die size for efficient pickup. The tip of the Teflon should be cut square and flat to ensure good vacuum to die surface. Ensure the Teflon tip remains clean from debris by inspecting under stereoscope.

During die attach, care must be exercised to ensure no tweezers touch the top of the die.

Wafer level testing is performed per the indicated specifications for dice. Considerable differences in performance can often be observed for dice versus packaged units due to the influences of packaging and assembly on certain devices and/or parameters. Please consult factory for more information on dice performance and lot qualifications via lot sampling test procedures.

Dice data sheet subject to change. Please consult factory for current revision in production.

I.D.No. 66-13-6200M

2

Linear Technology Corporation
1630 McCarthy Blvd., Milpitas, CA 95035-7417
(408) 432-1900 • FAX: (408) 434-0507 • www.linear.com

LT 1111 REV A • PRINTED IN USA


LINEAR TECHNOLOGY
© LINEAR TECHNOLOGY CORPORATION 2011